AMENDMENTS TO THE CLAIMS

Listing Of Claims

Claims 1-46 (Canceled)

- 47. (currently amended) A semiconductor component comprising:
- a semiconductor die comprising <u>a face and</u> a plurality of die contacts <u>on the face</u> in a pattern;
- a plurality of conductors on the <u>die face</u> in electrical communication with the die contacts configured to redistribute the pattern of the die contacts;
- a plurality of first contacts on the die face in electrical communication with the conductors; and
- a plurality of second contacts on the die <u>contacts</u> in electrical communication with the conductors configured for electrical contact by a test probe.

without electrical engagement of the first contacts.

- 48. (previously presented) The component of claim 47 wherein the first contacts comprise bumps in an area array.
- 49. (previously presented) The component of claim 47 further comprising an under bump metallization layer on each first contact.
- 50. (previously presented) The component of claim 47 wherein the second contacts comprise pads.
- 51. (previously presented) The semiconductor component of claim 47 wherein the component is contained on a wafer.

- 52. (previously presented) The component of claim 47 further comprising an electrically insulating layer between the die and the conductors.
- 53. (previously presented) The component of claim 47 wherein the conductors are configured to fan out or to fan in the pattern of the die contacts.
- 54. (currently amended) A semiconductor component comprising:
- a semiconductor die having a face and a plurality of die contacts on the face in a pattern;
- a plurality of conductors on the face in electrical communication with the die contacts configured to redistribute the pattern of the die contacts;
- an electrically insulating layer on the conductors having a plurality of openings <u>aligned with the die contacts</u>;
- a plurality of first contacts on the face in electrical communication with the conductors; and
- a plurality of second contacts on the face in electrical communication with the conductors comprising pads aligned with in the openings configured for electrical contact with a test probe.
- 55. (previously presented) The component of claim 54 wherein the pads comprise portions of the conductors.
- 56. (previously presented) The component of claim 54 wherein the component comprises a semiconductor wafer.

- 57. (previously presented) The semiconductor component of claim 54 wherein the first contacts comprise balls in a ball grid array and each ball of the ball grid array is in electrical communication with a second contact.
- 58. (currently amended) A semiconductor component comprising:
 - a semiconductor wafer;
- a plurality of components on the wafer, each component comprising a face and a plurality of die contacts on the face;
- a redistribution circuit on the wafer <u>face</u> comprising a plurality of conductors in electrical communication with the die contacts;
- a plurality of test contacts on the wafer <u>face</u> comprising non-oxidizing layers on portions of in electrical communication with the conductors; and
- a plurality of terminal contacts on the wafer <u>face</u> in electrical communication with the conductors.
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the test contacts configured for electrical contact by a test probe without interference from the terminal contacts, each test contact in electrical communication with a terminal contact.

- 59. (previously presented) The component of claim 58 wherein the terminal contacts comprise under bump metallization layers and solder bumps.
- 60. (previously presented) The component of claim 58 further comprising an electrically insulating layer on the

redistribution circuit having a plurality of openings aligned with the test contacts.

- 61. (previously presented) The component of claim 58 wherein the test contacts comprise portions of the conductors.
- 62. (previously presented) The component of claim 58 wherein the test probe comprises a needle probe, a buckle beam probe, a spring segment probe or a silicon probe.
- 63. (currently amended) A semiconductor component comprising:
- a semiconductor die comprising <u>a face and</u> a plurality of die contacts on the <u>face</u> in a pattern;
- a plurality of redistribution conductors on the die face in electrical communication with the die contacts;
- a plurality of bumped contacts on the die in electrical communication with face comprising under bump metallization layers on the conductors; and
- a plurality of test contacts on the <u>face comprising</u> non oxidizing layers on the conductors.

 die in electrical communication with the conductors, each test contact configured for electrical contact by a test probe without interference from the bumped contacts.
- 64. (previously presented) The component of claim 63 wherein the die is contained on a semiconductor wafer containing a plurality of dice substantially similar to the die.

- 65. (currently amended) The component of claim 63 wherein the bumped contacts comprise solder balls and under bump metallization layers in a grid array.
- 66. (previously presented) The component of claim 63 wherein the test contacts comprise portions of the redistribution conductors.
- 67. (currently amended) The component of claim 63 wherein the non oxidizing layers comprise a metal selected from the group consisting of Au and Pt. test contacts comprise separate pads.